The DS26C31 is a quad differential line driver designed for digital data transmission over balanced lines. The DS26C31T meets all the requirements of EIA standard RS-422 while retaining the low power characteristics of CMOS. The DS26C31M is compatible with EIA standard RS-422: however, one exception in test methodology is taken (Note 8). This enables the construction of serial and terminal interfaces while maintaining minimal power consumption.

The DS26C31 accepts TTL or CMOS input levels and translates these to RS-422 output levels. This part uses special output circuitry that enables the drivers to power down without loading down the bus. This device has enable and disable circuitry common to all four drivers. The DS26C31 is pin compatible to the AM26LS31 and the DS26LS31.

All inputs are protected against damage due to electrostatic discharge by diodes to $V_{\rm CC}$ and ground.

Dual-In-Line Package

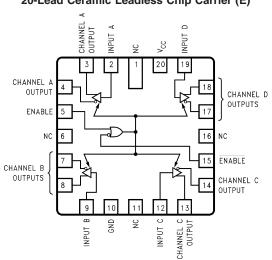
16 5 V

15

Connection Diagrams

INPUT A

- TTL input compatible
- Typical propagation delays: 6 ns
- Typical output skew: 0.5 ns
- Outputs will not load line when V_{CC} = 0V
- DS26C31T meets the requirements of EIA standard RS-422
- Operation from single 5V supply
- TRI-STATE outputs for connection to system buses
- Low quiescent current
- Available in surface mount
- Mil-Std-883C compliant



Truth Table

ENABLE	ENABLE	Input	Non-Inverting	Inverting	
			Output	Output	
L	L H		Z	Z	
All other		L	L	Н	
combinations of		Н	Н	L	
enable inputs					
L = Low logic =	state		•		

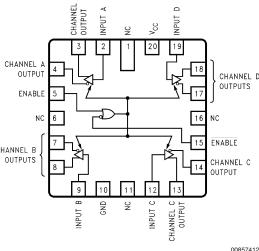
= Irrelevant

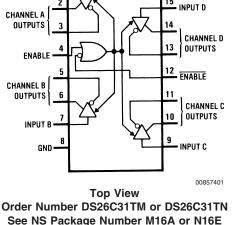
H = High logic state

Z = TRI-STATE (high impedance)

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For Complete Military Product Specifications, refer to the appropriate SMD or MDS. Order Number DS26C31ME/883, DS26C31MJ/883 or DS26C31MW/883 See NS Package Number E20A, J16A or W16A

June 1998

20-Lead Ceramic Leadless Chip Carrier (E)

Absolute Maximum Ratings (Notes 1,

2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Supply Voltage (V _{CC})	-0.5V to 7.0V
DC Input Voltage (V _{IN})	–1.5V to $V_{\rm CC}$
	+1.5V
DC Output Voltage (V _{OUT})	-0.5V to 7V
Clamp Diode Current (I _{IK} , I _{OK})	±20 mA
DC Output Current, per pin (I _{OUT})	±150 mA
DC V _{CC} or GND Current,	
per pin (I _{CC})	±150 mA
Storage Temperature Range (T _{STG})	–65°C to +150°C
Max. Power Dissipation (P _D) @25°C (N	lote 3)
Ceramic "J" Pkg.	2419 mW
Plastic "N" Pkg.	1736 mW

DC Electrical Characteristics

 $V_{CC} = 5V \pm 10\%$ (unless otherwise specified) (Note 4)

SOIC "M" Pkg.	1226 mW
Ceramic "W" Pkg.	1182 mW
Ceramic "E" Pkg.	2134 mW
Lead Temperature (T_L)	
(Soldering, 4 sec.)	260°C
This device does not meet 2000V ES	SD Rating. (Note 13)

Operating Conditions

	Min	Max	Units
Supply Voltage (V _{CC})	4.50	5.50	V
DC Input or Output Voltage			
(V _{IN} , V _{OUT})	0	$V_{\rm CC}$	V
Operating Temperature Range (T _A)			
DS26C31T	-40	+85	°C
DS26C31M	-55	+125	°C
Input Rise or Fall Times (t_r, t_f)		500	ns

Symbol	Parameter		Conditions	Min	Тур	Max	Units
V _{IH}	High Level Input Voltage			2.0			V
V _{IL}	Low Level Input Voltage					0.8	V
V _{он}	High Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{I}$ $I_{OUT} = -20 \text{ mA}$		2.5	3.4		V
V _{OL}	Low Level Output	$V_{IN} = V_{IH} \text{ or } V_{I}$	L,		0.3	0.5	V
	Voltage	I _{OUT} = 20 mA					
V _T	Differential Output	$R_L = 100\Omega$		2.0	3.1		V
	Voltage	(Note 5)					
$ V_T - \overline{V_T} $	Difference In	$R_L = 100\Omega$				0.4	V
	Differential Output	(Note 5)					
V _{os}	Common Mode	$R_L = 100\Omega$			1.8	3.0	V
	Output Voltage	(Note 5)					
$ V_{OS} - \overline{V_{OS}} $	Difference In	R _L = 100Ω				0.4	V
	Common Mode Output	(Note 5)					
IIN	Input Current	$V_{IN} = V_{CC}$, GND, V_{IH} , or V_{IL}				±1.0	μA
I _{cc}	Quiescent Supply	DS26C31T	$V_{IN} = V_{CC}$ or GND		200	500	μA
	Current (Note 6)	Ι _{ΟUT} = 0 μΑ	V _{IN} = 2.4V or 0.5V (Note 6)		0.8	2.0	mA
		DS26C31M	$V_{IN} = V_{CC}$ or GND		200	500	μA
		Ι _{ΟUT} = 0 μΑ	V _{IN} = 2.4V or 0.5V (Note 6)		0.8	2.1	mA
oz	TRI-STATE Output	V _{OUT} = V _{CC} or	GND				
	Leakage Current	ENABLE = V _{IL}			±0.5	±5.0	μA
		ENABLE = V _{IH}					
SC	Output Short	V _{IN} = V _{CC} or G	ND	-30		-150	mA
	Circuit Current	(Notes 5, 7)					
OFF	Output Leakage Current	DS26C31T	V _{OUT} = 6V			100	μA
	Power Off (Note 5)	$V_{\rm CC} = 0V$	V _{OUT} = -0.25V			-100	μA
		DS26C31M	V _{OUT} = 6V			100	μA
		$V_{\rm CC} = 0V$	$V_{OUT} = 0V$ (Note 8)			-100	μA

DC Electrical Characteristics (Continued)

Note 1: Absolute Maximum Ratings are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provide conditions for actual device operation.

Note 2: Unless otherwise specified, all voltages are referenced to ground. All currents into device pins are positive, all currents out of device pins are negative.

Note 3: Ratings apply to ambient temperature at 25°C. Above this temperature derate N package at 13.89 mW/°C, J package 16.13 mW/°C, M package 9.80 mW/°C, E package 12.20 mW/°C, and W package 6.75 mW/°C.

Note 4: Unless otherwise specified, min/max limits apply across the recommended operating temperature range. All typicals are given for V_{CC} = 5V and T_A = 25°C.

Note 5: See EIA Specification RS-422 for exact test conditions.

Note 6: Measured per input. All other inputs at $V_{\mbox{CC}}$ or GND.

Note 7: This is the current sourced when a high output is shorted to ground. Only one output at a time should be shorted.

Note 8: The DS26C31M (-55°C to +125°C) is tested with V_{OUT} between +6V and 0V while RS-422A condition is +6V and -0.25V.

Switching Characteristics

 V_{CC} = 5V ±10%, t_r \leq 6 ns, t_f \leq 6 ns (Figures 1, 2, 3, 4) (Note 4)

Symbol	Parameter	Conditions	Min	Тур	M	Units	
					DS26C31T	CS26C31M	1
t _{PLH} , t _{PHL}	Propagation Delays	S1 Open	2	6	11	14	ns
	Input to Output						
Skew	(Note 9)	S1 Open		0.5	2.0	3.0	ns
t _{TLH} , t _{THL}	Differential Output Rise	S1 Open		6	10	14	ns
	And Fall Times						
t _{PZH}	Output Enable Time	S1 Closed		11	19	22	ns
t _{PZL}	Output Enable Time	S1 Closed		13	21	28	ns
t _{PHZ}	Output Disable Time	S1 Closed		5	9	12	ns
	(Note 10)						
t _{PLZ}	Output Disable Time	S1 Closed		7	11	14	ns
	(Note 10)						
C _{PD}	Power Dissipation			50			pF
	Capacitance (Note 11)						
C _{IN}	Input Capacitance			6			pF

Note 9: Skew is defined as the difference in propagation delays between complementary outputs at the 50% point.

Note 10: Output disable time is the delay from ENABLE or ENABLE being switched to the output transistors turning off. The actual disable times are less than indicated due to the delay added by the RC time constant of the load.

Note 11: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC} 2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.

Comparison Table of Switching Characteristics into "LS-Type" Load

 $V_{CC} = 5V, T_A = 25^{\circ}C, t_r \le 6 \text{ ns}, t_f \le 6 \text{ ns}$ (*Figures 2, 4, 5, 6*) (Note 12)

Symbol	Parameter	Conditions	Conditions DS26	DS26C31T		DS26LS31C	
			Тур	Max	Тур	Max	
t _{PLH} , t _{PHL}	Propagation Delays	C _L = 30 pF					
	Input to Output	S1 Closed	6	8	10	15	ns
		S2 Closed					
Skew	(Note 9)	C _L = 30 pF					
		S1 Closed	0.5	1.0	2.0	6.0	ns
		S2 Closed					
t _{THL} , t _{TLH}	Differential Output Rise	C _L = 30 pF					
	and Fall Times	S1 Closed	4	6			ns
		S2 Closed					
t _{PLZ}	Output Disable Time	C _L = 10 pF					
	(Note 10)	S1 Closed	6	9	15	35	ns
		S2 Open					

Comparison Table of Switching Characteristics into "LS-Type"

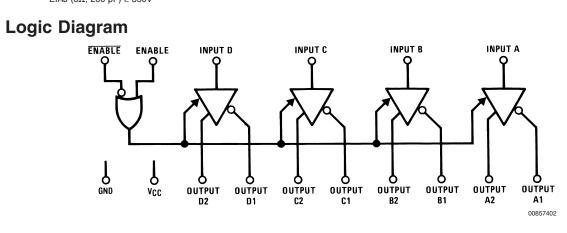
Load (Continued)

Symbol	Parameter	Conditions	DS26	C31T	DS26	_S31C	Units	
			Тур	Мах	Тур	Max		
t _{PHZ}	Output Disable Time	C _L = 10 pF						
	(Note 10)	S1 Open	4	7	15	25	ns	
		S2 Closed						
t _{PZL}	Output Enable Time	C _L = 30 pF						
		S1 Closed	14	20	20	30	ns	
		S2 Open						
t _{PZH}	Output Enable Time	C _L = 30 pF						
		S1 Open	11	17	20	30	ns	
		S2 Closed						

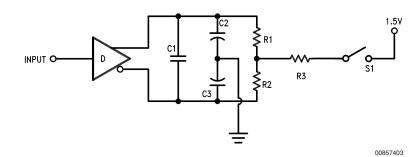
Note 12: This table is provided for comparison purposes only. The values in this table for the DS26C31 reflect the performance of the device but are not tested or guaranteed.

Note 13: ESD Rating:

 $\label{eq:HBM} \begin{array}{l} \text{HBM (1.5 k}\Omega, \ 100 \ \text{pF}) \\ \text{Inputs} \geq 1500 \text{V} \\ \text{Outputs} \geq 1000 \text{V} \\ \text{EIAJ (0}\Omega, \ 200 \ \text{pF}) \geq 350 \text{V} \end{array}$



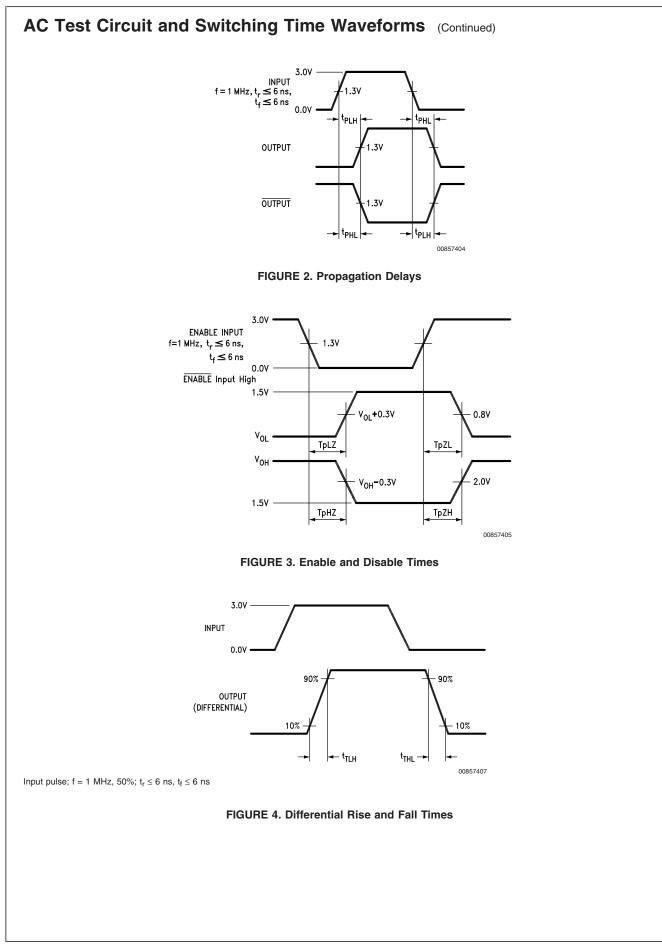
AC Test Circuit and Switching Time Waveforms

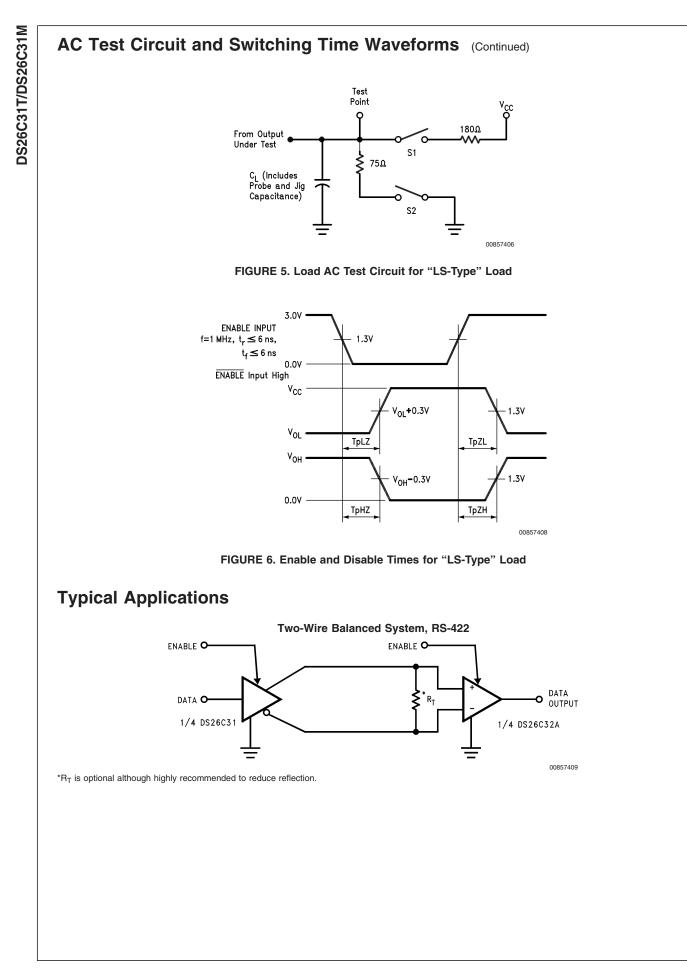


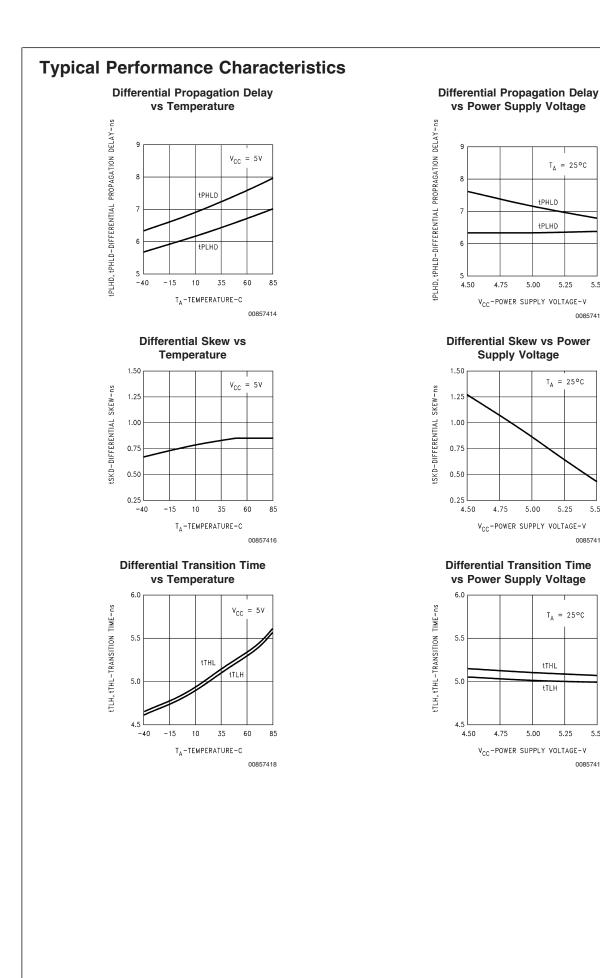
Note: C1 = C2 = C3 = 40 pF (Including Probe and Jig Capacitance), R1 = R2 = 50Ω , R3 = 500Ω .

FIGURE 1. AC Test Circuit

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5.25

5.50

00857415

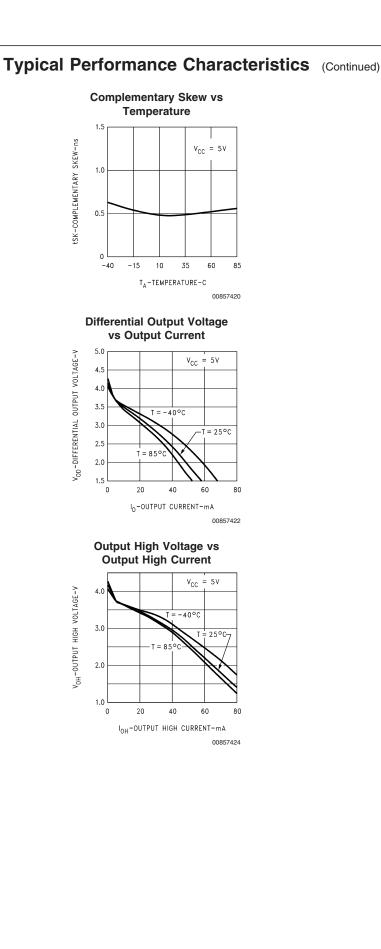
5.50

00857417

5.25

5.50

00857419



tSK-COMPLEMENTARY SKEW-ns 0.5 0 4.50 4.75 5.00 5.25 5.50 V_{CC}-POWER SUPPLY VOLTAGE-V 00857421 **Differential Output Voltage** vs Output Current 5.0 V_{OD}-DIFFERENTIAL OUTPUT VOLTAGE-V $T_A = 25°C$ 4.5 4.0 3.5 $c_{cc} = 5.5V$ 3.0 V_{CC} = 5.0V 2.5 V_{CC} = 4.52.0 1.5 0 20 40 60 80 IO-OUTPUT CURRENT-mA 00857423 **Output High Voltage vs Output High Current** $T_A = 25°C$ V_{OH}-OUTPUT HIGH VOLTAGE-V 4.0 = 5.5V = 5.0V V_{CC} 3.0

√_{cc}

20

40

I_{OH}-OUTPUT HIGH CURRENT-mA

60

80

00857425

2.0

1.0

0

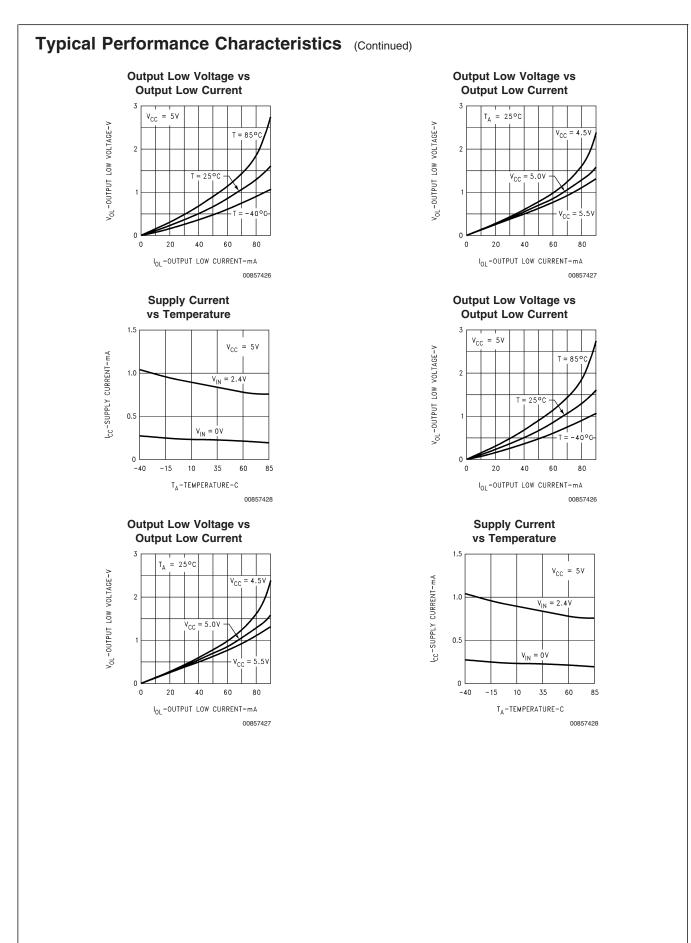
Complementary Skew vs

Power Supply Voltage

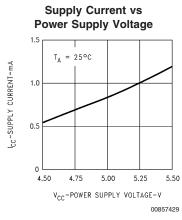
 $T_A = 25°C$

1.5

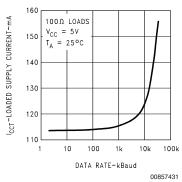
1.0



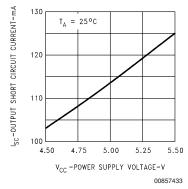
Typical Performance Characteristics (Continued)

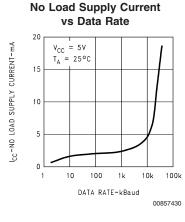


Loaded Supply Current vs Data Rate

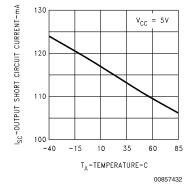


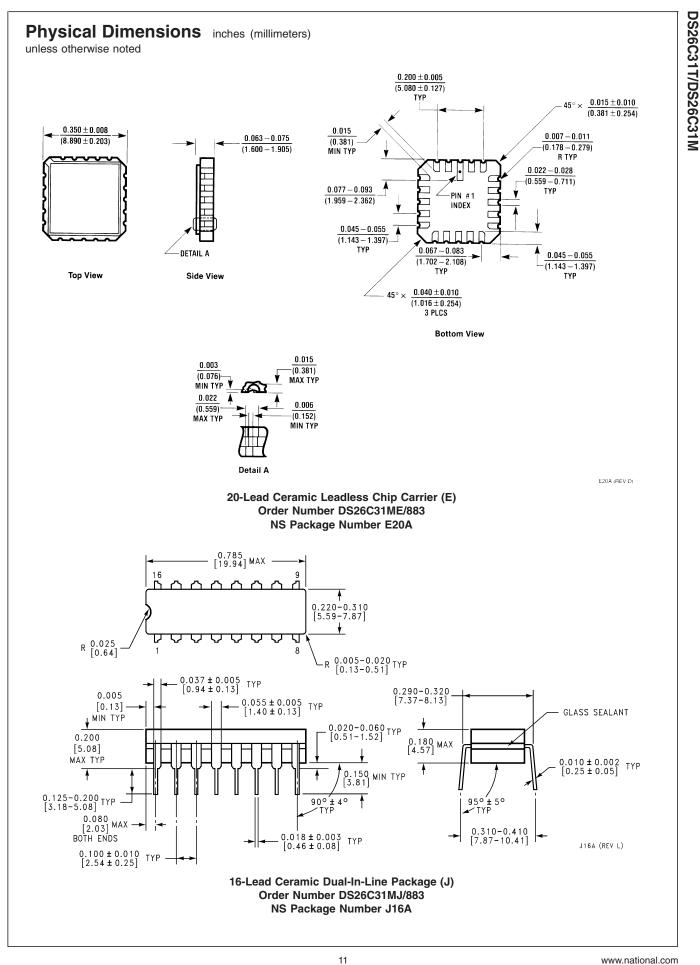
Output Short Circuit Current vs Power Supply Voltage



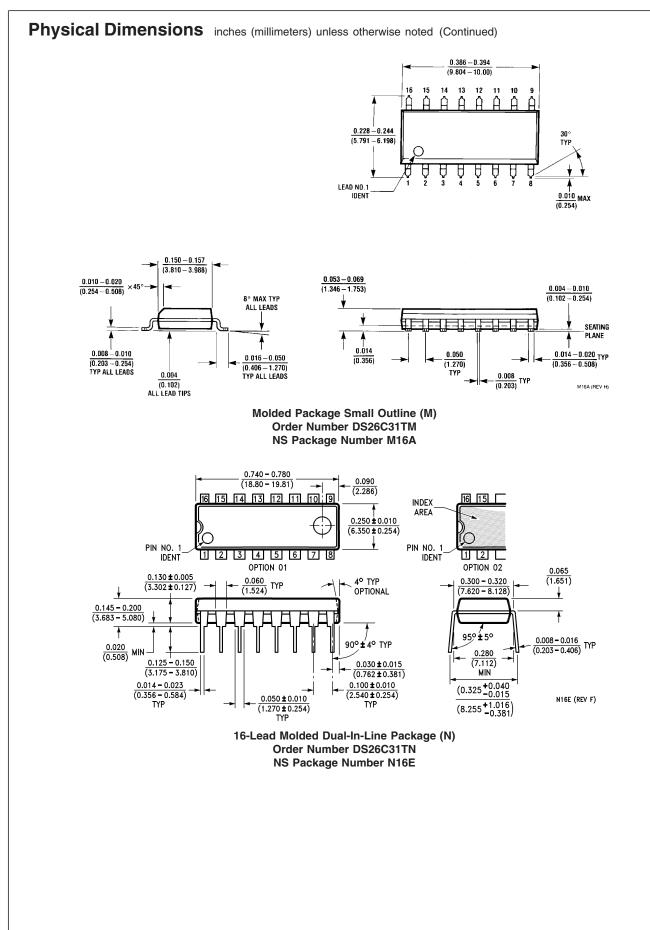


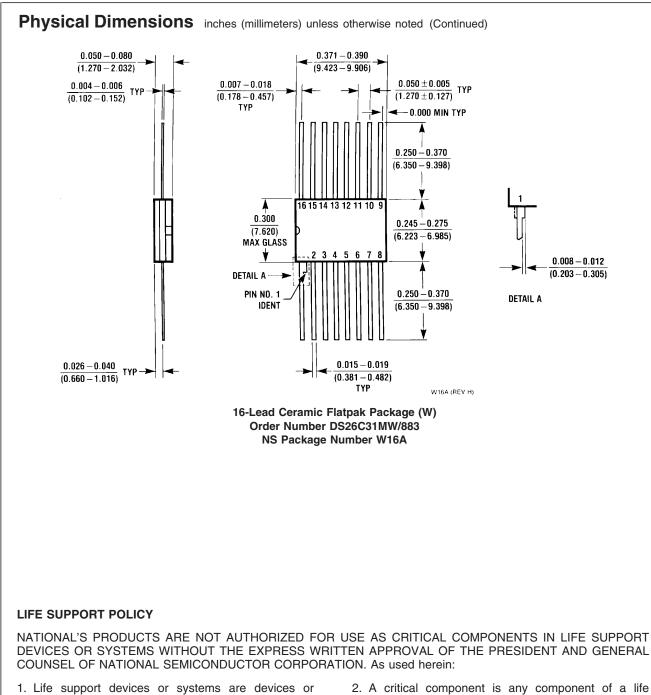
Output Short Circuit Current vs Temperature











- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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